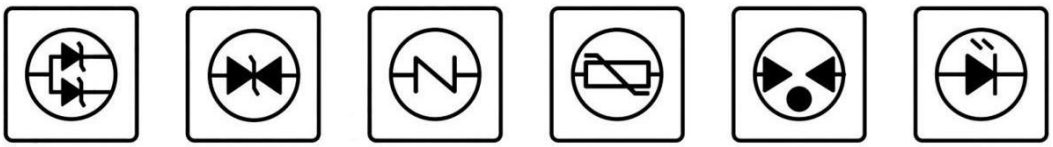
MSKSEMI 美森科
SEMICONDUCTOR



LM358

产品手册

产品简介

LM358 是一款双路低功耗的差分式运算放大器，可以单电源或双电源供电。具有较高的开环增益、内部补偿、高共模范围和良好的温度稳定性，以及具有输出短路保护的特点。广泛应用于传感器的放大电路、直流放大模块、音频放大电路和传统的运算放大电路中。

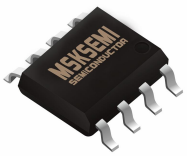
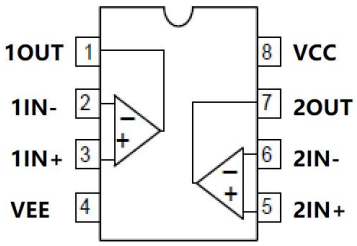
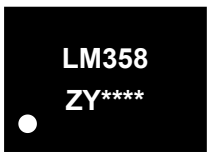
产品特点

- 内部频率补偿
- 短路保护
- 低功耗：典型值 0.5mA @V_{cc}=5V
- 封装形式：DIP-8、SOP-8
- 单电源电压范围：3V～36V
- 双电源电压范围：±18V
- 单位增益带宽:可达 1.2MHZ

产品用途

- 传感器信号放大器
- 直流增益
- 音频放大器
- 其它应用领域

封装形式和管脚功能定义

封装形式		管脚定义	丝印	
				
DIP-8	SOP-8		DIP-8	SOP-8

Notes :****Represent production order code

DIP-8/SOP-8 管脚序号	管脚定义	功能说明
1	1OUT	第 1路运放输出
2	1IN-	第 1路运放反相输入
3	1IN+	第 1路运放正相输入
4	VEE	负电源
5	2IN+	第2路运放正相输入
6	2IN-	第2路运放反相输入
7	2OUT	第2路运放输出
8	VCC	正电源

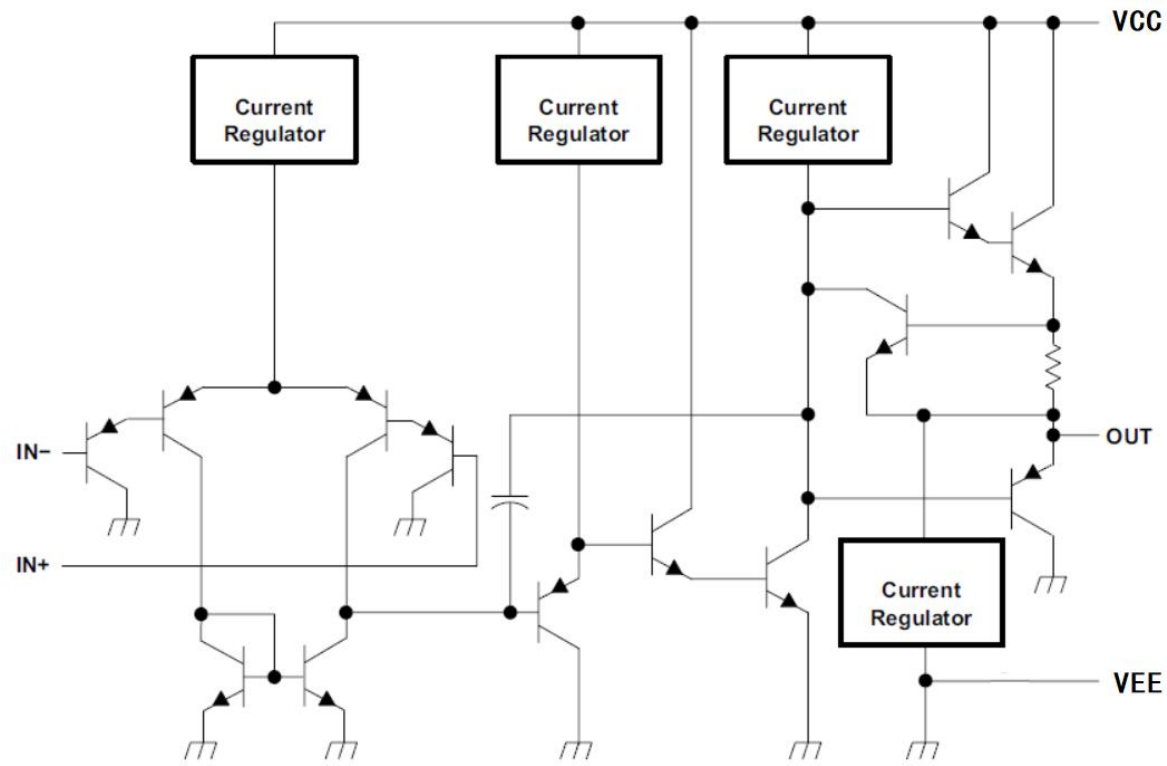
极限参数

项目	符号	极限值(1)	单位
单电源供电电压	V_{cc}	40	V
双电源供电电压	Vs	±20	V
差分输入电压(2)	V_{ID}	±40	V
共模输入电压	V_{ICR}	-0.3～40V	V
输出短路时间	t_{sc}	连续	
耗散功率	P_D	400	mW
工作温度	T_A	0-70	℃
储存温度	T_S	-65-150	℃
焊接温度	T_W	260,10s	℃

注：（1）极限值是指无论在任何条件下都不能超过的极限值。如果达到此极限值，将有可能造成产品劣化等物理性损伤；同时在接近极限参数下，不能保证芯片可以正常工作。

（2）输入端 IN+相对于 IN-之间的电压差。

等效原理图

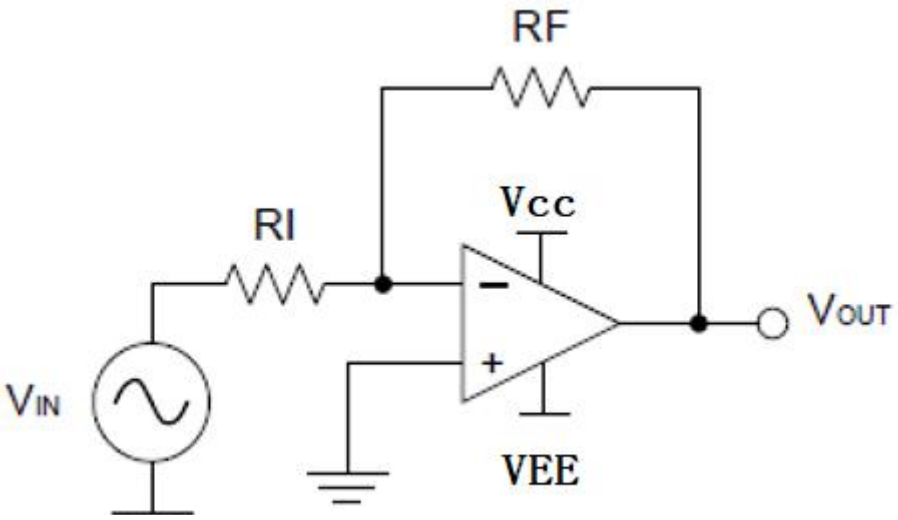


直流电学特性 （T_A=25℃， VCC=5V, VEE=GND 除非特别指定）

项目	符号	测试条件		最小值	典型值	最大值	单位
输入失调电压	V_{IO}	VCC=5V to MAX, V_{IC}=V_{ICR} (min), VO=1.4V		_	5	_	mV
输入失调电流	I_{IO}	VO = 1.4 V		–	10	50	nA
偏置电流	I_{BIAS}	VO = 1.4 V		–	50	250	nA
共模输入电压	V_{ICR}	VCC=5V to 36V		VEE	_	VCC-1.5V	V
开环电压增益	A_{OL}	VCC=15V, VO=1V to 11V, RL≥2k Ω			100	_	V/mV
共模抑制比	CMRR	VCC=5V to MAX, V_{IC}=V_{ICR} (min)		_	80	_	dB
单位增益带宽	GBWP			_	1.2	_	MHZ
电源电压抑制比P_{SSR}	$\Delta V_{VDD}/\Delta V_{IO}$	VCC=5V to MAX, f=20kHz		–	90	–	dB
串扰衰减抑制比CS	V_{O1}/V_{O2}	f=1kHz to 20kHz		_	120	_	dB
输出高电平电压	VOH	VCC=15V, V_{ID}=1V	Iout =-50uA	_	13.6	_	V
			Iout =-1mA	_	13.5	_	V
			Iout =-5mA	_	13.4	_	V
		VCC=28V	RL=2k		26	–	V
输出低电平电压	VOL	VCC=15V, V_{ID}=-1V	Iout =50uA	_	0.1	_	V
			Iout =1mA	_	0.7	_	V
			Iout =5mA	_	1.0	_	V
		VCC=28V	RL=2k	–	0.85	–	V
输出短路电流	I_{OS}	VCC=5V, VEE=-5V, VO=0V		–	±24	–	mA
电源工作电流	I_{CC}	VCC=5V, VO=1/2VCC, No load		–	0.5	–	mA
		VCC=36, VO=1/2VCC, No load		_	0.8	_	mA
单电源工作电压	VCC	VEE=0V (GND)		3	_	36	V
双电源工作电压	VS	VCC, VEE		-18	–	+18	V

典型应用

1、线路图



2、设计要求

必须选择大于输入电压范围和输出范围的电源电压。

例如，将信号源 VIN 从±0.5 V 放大到±1.8V。将电源设置为± 5 V 足以适应此应用要求。

3、设计过程

根据公式(1)计算放大倍数(增益) A_V

A_V =-VO/VIN ------(1)

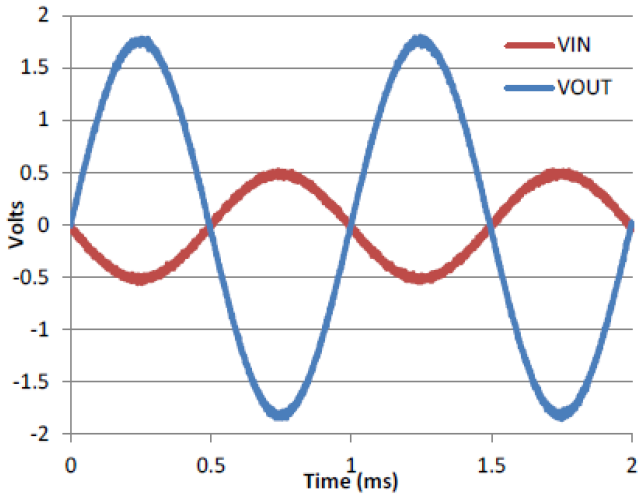
A_V =-VO/VIN=-1.8/0.5=-3.6

一旦确定了所需的增益 A_V，就要为 RI 或 RF 电阻选择一个值。根据运放的电特性及功耗的需要，可选择 1kΩ-100kΩ范围内的值。本例将选择 RI=10 kΩ，则 RF=36kΩ。这由方程式 2 确定。

A_V =-RF/RI ---------(2)

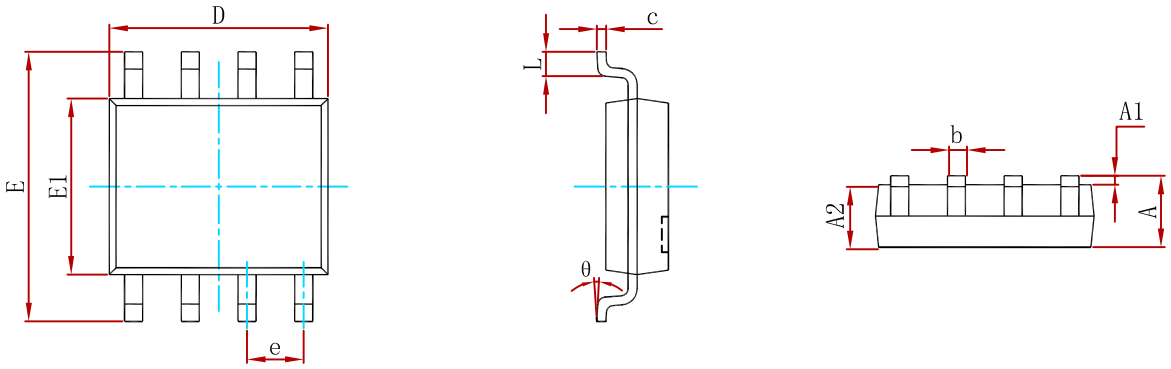
RF= $-A_V$ * RI=3.6*10 = 36 kΩ

4、应用曲线图



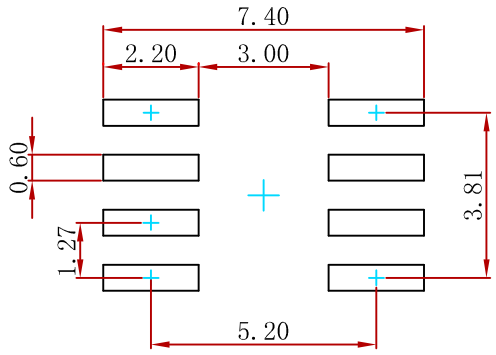
反相放大器的输入电压 VS 输出电压

封装信息



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	**Max**	**Min**	**Max**
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270（BSC）		0.050（BSC）	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

焊盘尺寸建议

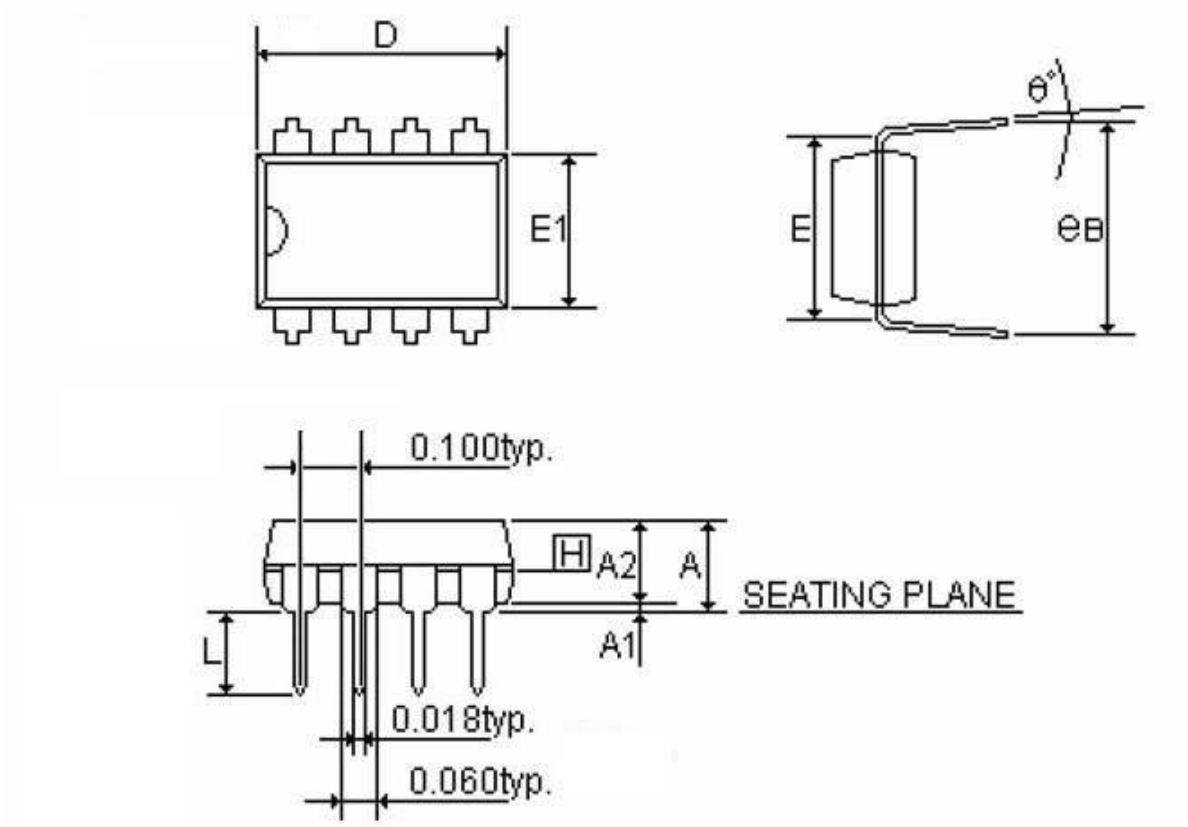


Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.05mm.
3.The pad layout is for reference purposes only.

订购信息

P/N	PKG	QTY
LM358	SOP-8	2500

DIP 8



SYMBOLS	MIN	NOR	MAX	MIN	NOR	MAX
	(inch)			(mm)		
A	-	-	0.210	-	-	5.334
A1	0.015	-	-	0.381	-	-
A2	0.125	0.130	0.135	3.175	3.302	3.429
D	0.435	0.455	0.475	15.669	16.050	16.685
E		0.300			7.62	
E1	0.245	0.250	0.255	6.223	6.35	6.477
L	0.115	0.130	0.150	2.921	3.302	3.810
e B	0.335	0.355	0.375	8.509	9.017	9.525
θ°	0°	7°	15°	0°	7°	15°

订购信息

P/N	PKG	QTY
LM358	DIP-8	50

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